

ELECTRICAL SPECIFICATIONS (at 25°C unless noted)

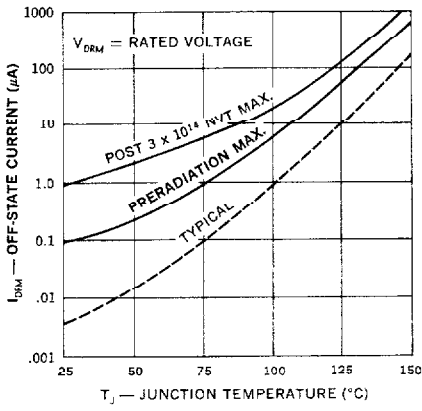
Test	Symbol	Preradiation Limits			Post 3×10^{14} NVT Design Limits		Units	Test Conditions
		Min.	Typ.	Max.	Min.	Max.		
SUBGROUP 1 Visual and Mechanical								
MIL-STD-750 Method 20/1								
SUBGROUP 2 (25°C Tests)								
Off-State Current	I_{DRM}	—	.005	0.1	—	1.0	μA	$R_{GK} = 220\Omega, V_{DRM} = \text{Rating}$
Reverse Gate Current	I_{CR}	—	.01	0.1	—	1.0	μA	$V_{GR} = 2V$
Input Trigger Current (Note 2)	I_{ST}	1.8	2.3	3.5	—	20	mA	$R_{GK} = 220\Omega, V_D = 5V$
Gate Trigger Voltage	V_{GT}	0.4	0.5	0.7	—	1.5	V	$R_{GK} = 220\Omega, V_D = 5V$
On-State Voltage	V_T	0.8	1.1	1.5	—	3.0	V	$i_T = 1A$ (pulse test)
Holding Current	I_{H}	0.3	0.7	10	—	30	mA	$R_{GK} = 220\Omega$
SUBGROUP 3 (25°C Tests)								
Off-State Voltage-Critical Rate of Rise	dv_c/dt	20	40	—	—	—	V/ μS	$R_{GK} = 220\Omega, V_D = 30V$
Gate Trigger-on Pulse Width	t_{pg} (on)	—	.02	.05	—	0.1	μS	$I_G = 25mA, I_T = 1A, V_D = 30V$
Delay Time	t_d	—	.02	—	—	—	μS	$I_G = 25mA, I_T = 1A, V_D = 30V$
Rise Time	t_r	—	.05	—	—	—	μS	$I_G = 25mA, I_T = 1A, V_D = 30V$
Circuit Commutated Turn-off Time	t_q	—	1.5	2.5	—	1.0	μS	$I_T = 1A, I_R = 1A, R_{GK} = 220\Omega$
SUBGROUP 4 (125°C Tests)								
High Temp Off-State Current	I_{DRM}	—	10	100	—	100	μA	$R_{GK} = 220\Omega, V_{DRM} = \text{Rating}$
High Temp Gate Trigger Voltage	V_{GT}	0.1	.17	—	0.1	—	V	$R_{GK} = 220\Omega, V_D = 5V$

- Notes: 1. Off-State voltage ratings apply over the operating temperature range provided the gate is connected to the cathode through an appropriate resistor, or other adequate bias is used.
2. Total Input Trigger Current, including current required by 220 Ω gate bias resistance.

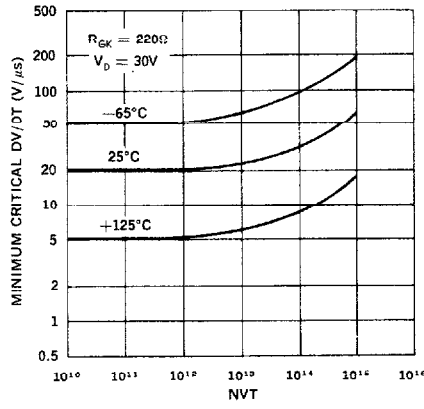
DESIGN CONSIDERATIONS

- Curve 1 shows the off-state current, I_{DRM} of the SCR as a function of temperature. I_{DRM} is increased by radiation damage, but is not a design consideration at the recommended gate bias levels.
In order to optimize for radiation tolerance, reverse blocking capability has not been retained as a design feature. Devices with reverse blocking capability can be provided.
- Minimum critical dv/dt levels are defined in Curve 2. The dv/dt capability is improved after radiation because of reduced triggering sensitivity. dv/dt is therefore a design consideration only prior to radiation.
- Curves 3 and 4 show the limits of Gate Trigger Voltage and Total Input Trigger Current prior to radiation. Maximum design limits after a total radiation dosage of 3×10^{14} NVT is also shown. Curves 5 and 6 show the maximum limits of Gate Trigger Voltage and Total Input Trigger Currents as a junction of neutron dosage. The minimum level of Trigger current prior to radiation is established by the shunting effect of a 220 ohm resistor between gate and cathode. After radiation the device is less sensitive and Total Trigger Current will increase to a level relatively independent of the bias resistance. The 220 ohm resistor is recommended since it raises the minimum preradiation trigger current to a level that is closer to the post radiation limit and minimizes the percentage change in this parameter.
- Current ratings shown in Curves 10, 11, and 12 apply after the device has been subjected to 3×10^{14} NVT. Current ratings prior to radiation are greater than the values indicated.
- Gamma radiation produces a reversible ionization (leakage) current within the device which is directly proportional to the Gamma flux level. When the Gamma flux level is in the range of 10 to 100 Roentgens per microsecond for burst durations greater than 1 microsecond, the device will self trigger ON. For the radiation bursts associated with nuclear explosions, the Gamma flux level will invariably cause device triggering at radiation levels significantly below the levels that would produce detectable permanent device damage due to cumulative neutron dosage. In applications where the burst effect triggering cannot be tolerated, it is necessary to reset the device after the radiation burst. Special circuit approaches such as additional SCRs to crowbar or otherwise cancel the output function may be used.

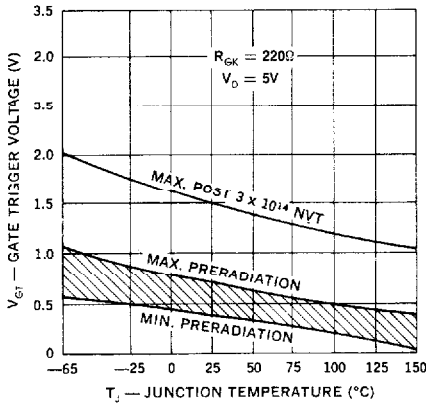
1. Off-State Current



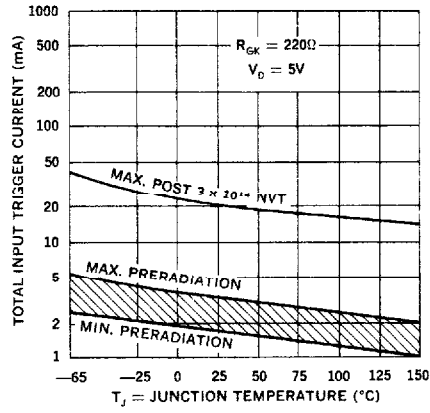
2. Minimum Critical DV/DT vs. Neutron Dosage



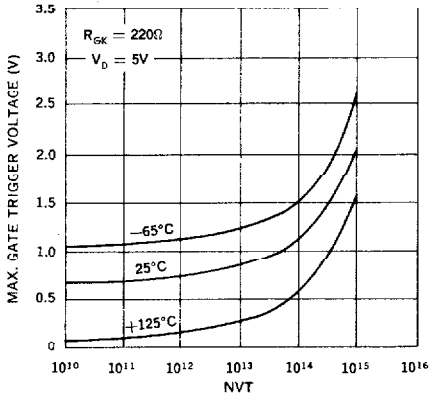
3. Gate Trigger Voltage



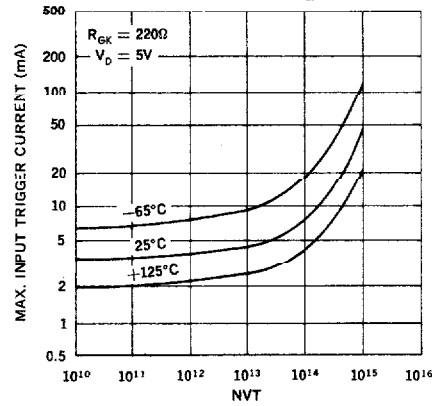
4. Input Trigger Current



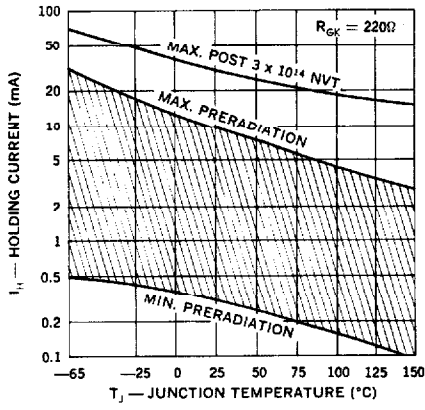
5. Max. Gate Trigger Voltage vs. Neutron Dosage



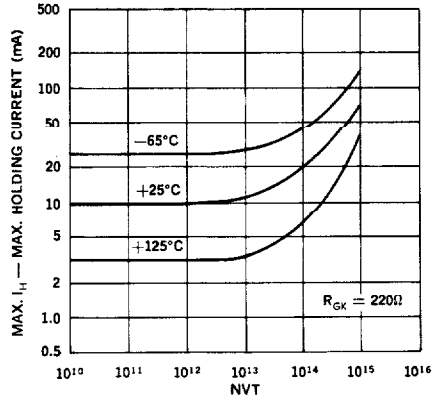
6. Max. Input Trigger Current vs. Neutron Dosage



7. Holding Current

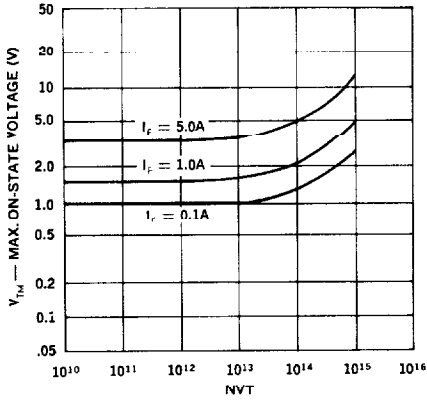


8. Max. Holding Current vs. Neutron Dosage

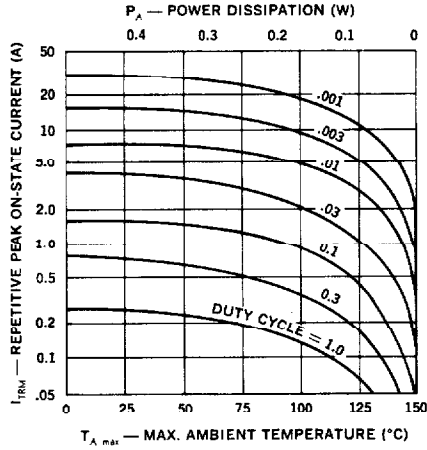


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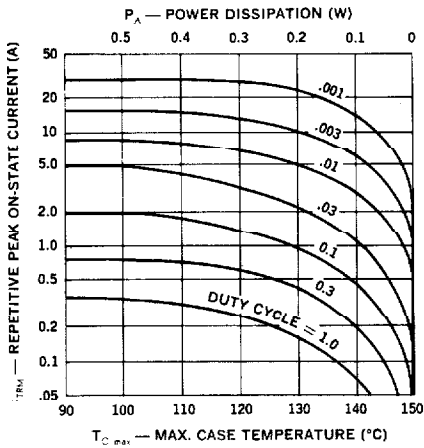
9. Max. On-State Voltage vs. Neutron Dosage



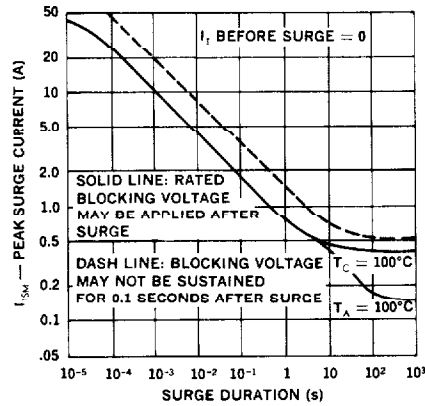
10. Peak Current vs. Ambient Temperature



11. Peak Current vs. Case Temperature



12. Surge Current vs. Time





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